800-900 MHz +36 dBm Power GaAs FET

August 2006 - Rev 03-Aug-06

Features

- **High Gain**
- □ +36 dBm Power Output
- Proprietary Power FET Process
- □ >45% Linear Power Added Efficiency
- □ +33 dBm with 30 dBc Third Order Products

Applications

- □ ISM Band Base Stations
- **Cellular Base Stations**
- □ Wireless Local Loop

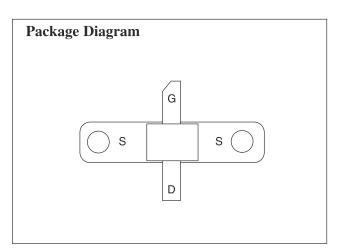
Description

The CFH2162-P1 is a high-gain, linear FET intended for driver amplifier applications in high-power systems, and output stage usage in medium power applications at power levels up to +36 dBm. The device is easily matched and pro-

Specifications (TA = 25° C) The following specifications are guaranteed at room temperature in Celeritek test fixture at 850 MHz.

Parameters	Conditions	Min	Тур	Max	Units	
$V_d = 10V, I_d = 1100 \text{ mA} (Quiescent)$						
P _{-1dB}		36.0	37.0		dBm	
G _{-1 dB}		19.0	20.0		dB	
3rd Order Products ⁽¹⁾		30	35		dBc	
Efficiency	@ P1dB		45		%	
$V_d = 8V, I_d = 1300 \text{ mA} \text{ (Quiescent)}$						
P _{-1dB}			36.0	_	dBm	
G _{-1 dB}		_	19.0	_	dB	

Parameters	Conditions	Min	Тур	Max	Units
g _m	Vds = 2.0V, Vgs = 0V	—	1700	_	mS
Idss	Vds = 2.0V, Vgs = 0V	—	2.8	—	А
Vp	Vds = 3.0V, Ids = 65 mA	—	-1.8		Volts
BVGD	Igd = 6.5 mA	20	24	_	Volts
$\Theta_{JL}(2)$	@150°C TCH	—	8	—	°C/W



vides excellent linearity at 4 Watts. Manufactured in Celeritek's proprietary power FET process, this device is assembled in a power flange package.

Absolute Maximum Ratings

Parameter	Symbol	Rating
Drain-Source Voltage	VDS	15V ⁽³⁾
Gate-Source Voltage	V _{GS}	-5V
Drain Current	IDS	Idss
Continuous Dissipation	PT	10W
Channel Temperature	TCH	175°C
Storage Temperature	TSTG	-65°C to +175°C

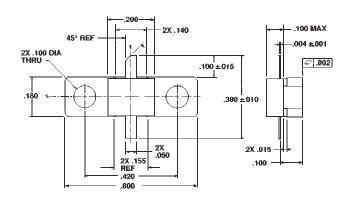
Notes:

1. Sum to two tones with 1 MHz spacing = 33 dBm.

2. See thermal considerations information.

3. Maximum potential difference across the device (Vd + Vg) cannot exceed 18V.

Power Flange Package Physical Dimensions



Mimix Broadband, Inc., 10795 Rockley Rd., Houston, Texas 77099 Tel: 281.988.4600 Fax: 281.988.4615 mimixbroadband.com Page 1 of 2

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BROADBAND

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Ordering Information

The CFH2162-P1 power stage is available in a SOIC-8 surface mount package. Devices are available in tape and reel. Ordering part numbers are listed.

Part Number for Ordering CFH2162-P1 <u>Function</u> 800 - 900 MHz Power Stage Package Power flange package

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